

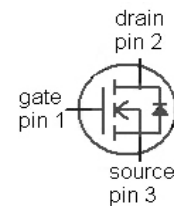
**OptiMOS® Power-Transistor**
**Features**

- For fast switching converters and sync. rectification
- N-channel enhancement - normal level
- 175 °C operating temperature
- Avalanche rated
- Pb-free lead plating, RoHS compliant


**Product Summary**

|                  |      |    |
|------------------|------|----|
| $V_{DS}$         | 60   | V  |
| $R_{DS(on),max}$ | 14.4 | mΩ |
| $I_D$            | 50   | A  |

|                |              |
|----------------|--------------|
| <b>Type</b>    | IPD144N06N G |
|                |              |
| <b>Package</b> | PG-TO252-3   |
| <b>Marking</b> | 144N06N      |


**Maximum ratings, at  $T_j=25\text{ °C}$ , unless otherwise specified**

| Parameter                           | Symbol         | Conditions   | Value       | Unit              |
|-------------------------------------|----------------|--|-------------|-------------------|
| Continuous drain current            | $I_D$          | $T_C=25\text{ °C}^{1)}$  | 50          | A                 |
|                                     |                | $T_C=100\text{ °C}$  | 45          |                   |
| Pulsed drain current                | $I_{D,pulse}$  | $T_C=25\text{ °C}^{2)}$  | 200         |                   |
| Avalanche energy, single pulse      | $E_{AS}$       | $I_D=50\text{ A}, R_{GS}=25\text{ }\Omega$   | 240         | mJ                |
| Reverse diode $dv/dt$               | $dv/dt$        | $I_D=50\text{ A}, V_{DS}=48\text{ V},$<br>$di/dt=200\text{ A}/\mu\text{s},$<br>$T_{j,max}=175\text{ °C}$ | 6           | kV/ $\mu\text{s}$ |
| Gate source voltage                 | $V_{GS}$       |  | $\pm 20$    | V                 |
| Power dissipation                   | $P_{tot}$      | $T_C=25\text{ °C}$   | 136         | W                 |
| Operating and storage temperature   | $T_j, T_{stg}$ |  | -55 ... 175 | °C                |
| IEC climatic category; DIN IEC 68-1 |                |  | 55/175/56   |                   |

<sup>1)</sup> Current is limited by bondwire; with an  $R_{thJC}=1.1\text{ K/W}$  the chip is able to carry 64 A.

<sup>2)</sup> See figure 3

| Parameter | Symbol | Conditions | Values |      |      | Unit |
|-----------|--------|------------|--------|------|------|------|
|           |        |            | min.   | typ. | max. |      |

**Thermal characteristics**

|                                     |            |  |   |   |     |     |
|-------------------------------------|------------|--|---|---|-----|-----|
| Thermal resistance, junction - case | $R_{thJC}$ |  | - | - | 1.1 | K/W |
| SMD version, device on PCB          | $R_{thJA}$ | minimal footprint                            | - | - | 75  |     |
|                                     |            | 6 cm <sup>2</sup> cooling area <sup>3)</sup> | - | - | 50  |     |

**Electrical characteristics, at  $T_j=25\text{ }^\circ\text{C}$ , unless otherwise specified**
**Static characteristics**

|                                  |               |  |     |      |      |               |
|----------------------------------|---------------|--|-----|------|------|---------------|
| Drain-source breakdown voltage   | $V_{(BR)DSS}$ | $V_{GS}=0\text{ V}, I_D=1\text{ mA}$                                   | 60  | -    | -    | V             |
| Gate threshold voltage           | $V_{GS(th)}$  | $V_{DS}=V_{GS}, I_D=80\text{ }\mu\text{A}$                             | 2.1 | 3    | 4    |               |
| Zero gate voltage drain current  | $I_{DSS}$     | $V_{DS}=60\text{ V}, V_{GS}=0\text{ V}, T_j=25\text{ }^\circ\text{C}$  | -   | 0.01 | 1    | $\mu\text{A}$ |
|                                  |               | $V_{DS}=60\text{ V}, V_{GS}=0\text{ V}, T_j=125\text{ }^\circ\text{C}$ | -   | 1    | 100  |               |
| Gate-source leakage current      | $I_{GSS}$     | $V_{GS}=20\text{ V}, V_{DS}=0\text{ V}$                                | -   | 10   | 100  | nA            |
| Drain-source on-state resistance | $R_{DS(on)}$  | $V_{GS}=10\text{ V}, I_D=50\text{ A}$                                  | -   | 11.3 | 14.4 | m $\Omega$    |
| Gate resistance                  | $R_G$         |  | -   | 1.5  | -    | $\Omega$      |
| Transconductance                 | $g_{fs}$      | $ V_{DS} >2 I_D R_{DS(on)max}, I_D=50\text{ A}$                        | 26  | 53   | -    | S             |

<sup>3)</sup> Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm<sup>2</sup> (one layer, 70  $\mu\text{m}$  thick) copper area for drain connection. PCB is vertical in still air.

| Parameter | Symbol | Conditions | Values |      |      | Unit |
|-----------|--------|------------|--------|------|------|------|
|           |        |            | min.   | typ. | max. |      |

**Dynamic characteristics**

|                              |              |   |   |      |      |    |
|------------------------------|--------------|---|---|------|------|----|
| Input capacitance            | $C_{iss}$    | $V_{GS}=0\text{ V}, V_{DS}=30\text{ V},$<br>$f=1\text{ MHz}$                    | - | 1400 | 1900 | pF |
| Output capacitance           | $C_{oss}$    |   | - | 400  | 530  |    |
| Reverse transfer capacitance | $C_{rss}$    |   | - | 100  | 150  |    |
| Turn-on delay time           | $t_{d(on)}$  | $V_{DD}=30\text{ V}, V_{GS}=10\text{ V},$<br>$I_D=50\text{ A}, R_G=7.2\ \Omega$ | - | 11   | 18   | ns |
| Rise time                    | $t_r$        |   | - | 35   | 53   |    |
| Turn-off delay time          | $t_{d(off)}$ |   | - | 29   | 43   |    |
| Fall time                    | $t_f$        |   | - | 11   | 17   |    |

**Gate Charge Characteristics<sup>4)</sup>**

|                          |               |  |   |     |    |    |
|--------------------------|---------------|--|---|-----|----|----|
| Gate to source charge    | $Q_{gs}$      | $V_{DD}=30\text{ V}, I_D=50\text{ A},$<br>$V_{GS}=0\text{ to }10\text{ V}$ | - | 8   | 10 | nC |
| Gate charge at threshold | $Q_{g(th)}$   |  | - | 4   | 6  |    |
| Gate to drain charge     | $Q_{gd}$      |  | - | 18  | 27 |    |
| Switching charge         | $Q_{sw}$      |  | - | 22  | 32 |    |
| Gate charge total        | $Q_g$         |  | - | 41  | 54 |    |
| Gate plateau voltage     | $V_{plateau}$ |  | - | 5.5 | -  | V  |
| Output charge            | $Q_{oss}$     | $V_{DD}=30\text{ V}, V_{GS}=0\text{ V}$                                    | - | 14  | 19 |    |

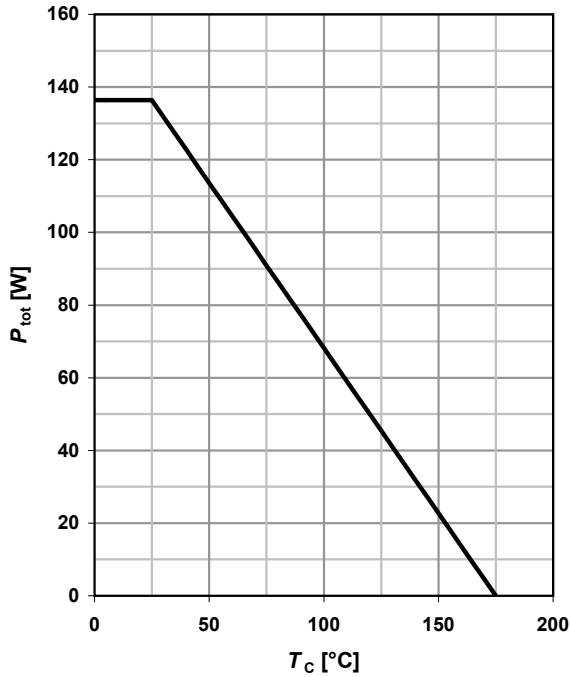
**Reverse Diode**

|                                  |               |   |   |      |     |    |
|----------------------------------|---------------|---|---|------|-----|----|
| Diode continuous forward current | $I_S$         | $T_C=25\text{ }^\circ\text{C}$  | - | -    | 50  | A  |
| Diode pulse current              | $I_{S,pulse}$ |   | - | -    | 200 |    |
| Diode forward voltage            | $V_{SD}$      | $V_{GS}=0\text{ V}, I_F=50\text{ A},$<br>$T_j=25\text{ }^\circ\text{C}$ | - | 0.94 | 1.3 | V  |
| Reverse recovery time            | $t_{rr}$      | $V_R=30\text{ V}, I_F=I_S,$<br>$di_F/dt=100\text{ A}/\mu\text{s}$       | - | 45   | 56  | ns |
| Reverse recovery charge          | $Q_{rr}$      |   | - | 74   | 93  | nC |

<sup>4)</sup> See figure 16 for gate charge parameter definition

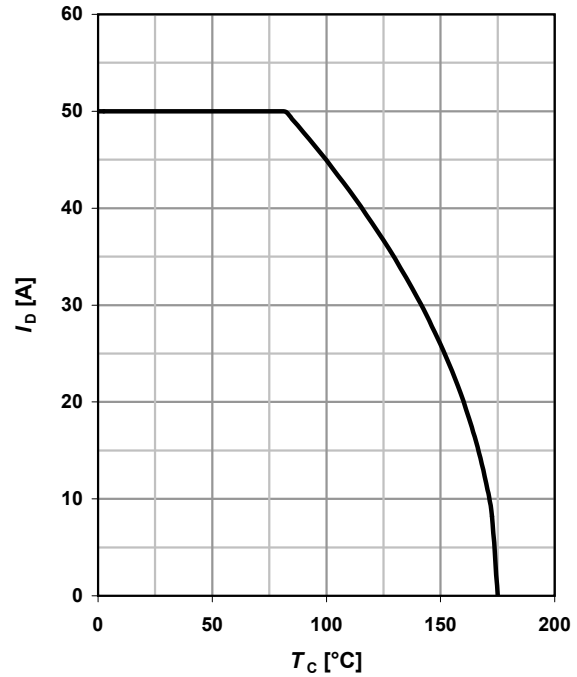
**1 Power dissipation**

$P_{tot}=f(T_C); V_{GS} \geq 6 \text{ V}$



**2 Drain current**

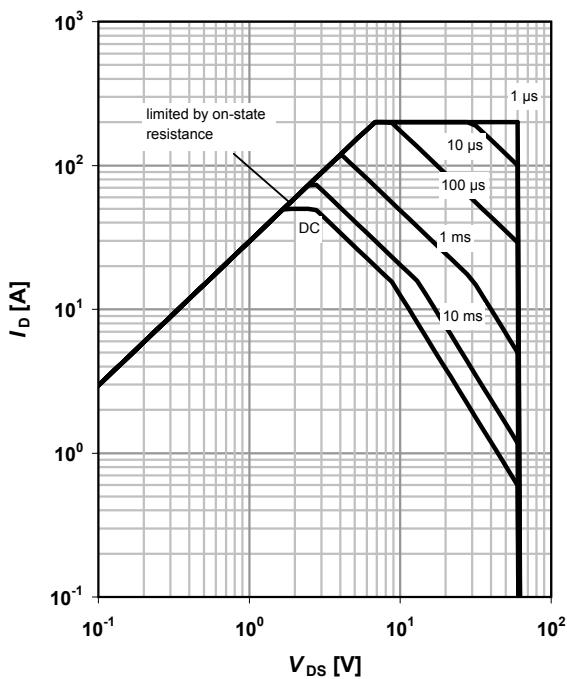
$I_D=f(T_C); V_{GS} \geq 10 \text{ V}$



**3 Safe operating area**

$I_D=f(V_{DS}); T_C=25 \text{ °C}; D=0$

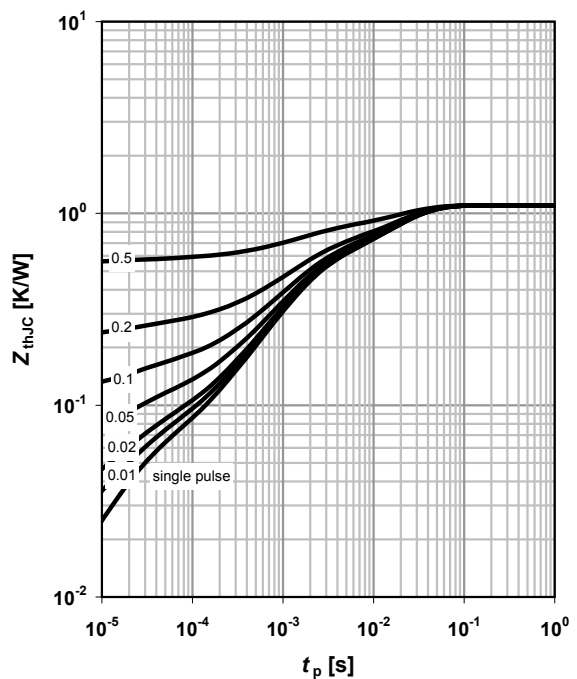
parameter:  $t_p$



**4 Max. transient thermal impedance**

$Z_{thJC}=f(t_p)$

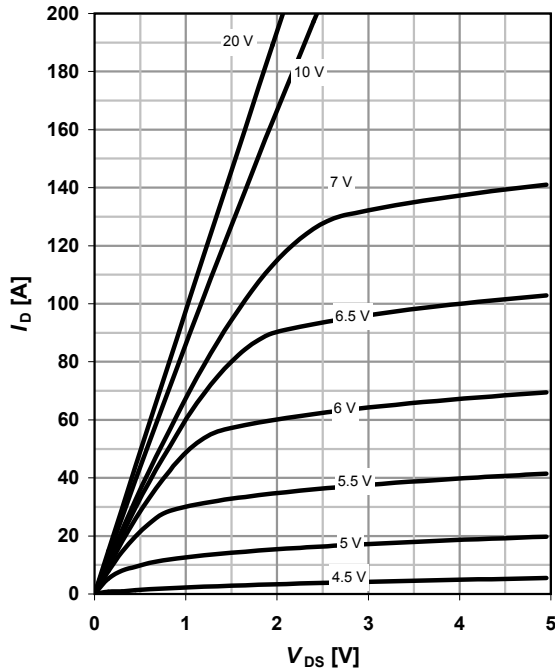
parameter:  $D=t_p/T$



**5 Typ. output characteristics**

$I_D = f(V_{DS}); T_j = 25\text{ }^\circ\text{C}$

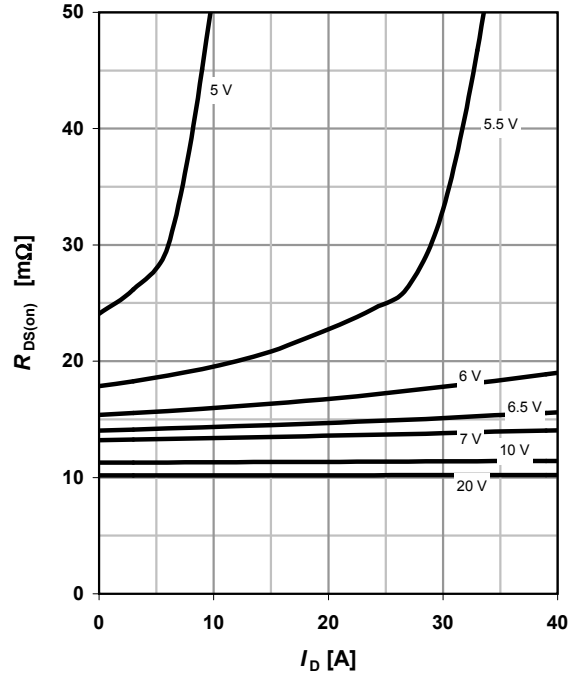
parameter:  $V_{GS}$



**6 Typ. drain-source on resistance**

$R_{DS(on)} = f(I_D); T_j = 25\text{ }^\circ\text{C}$

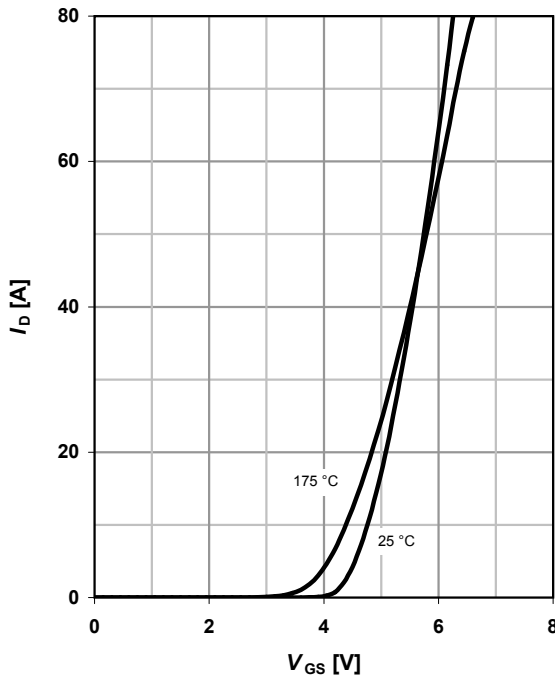
parameter:  $V_{GS}$



**7 Typ. transfer characteristics**

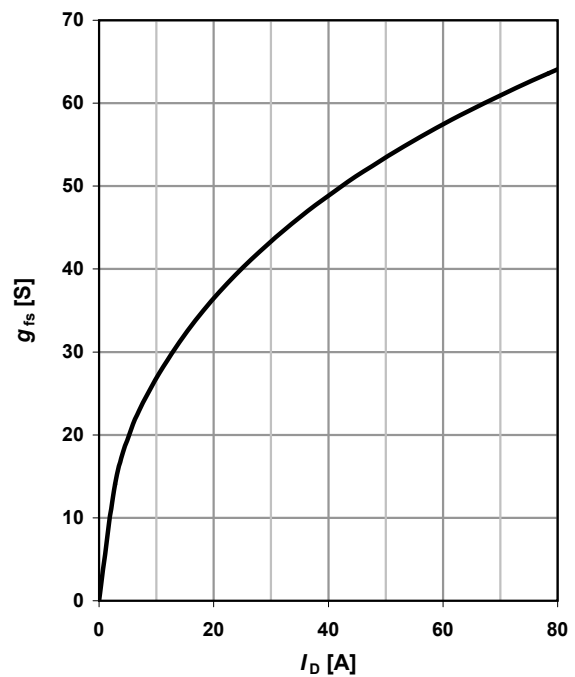
$I_D = f(V_{GS}); |V_{DS}| > 2|I_D|R_{DS(on)max}$

parameter:  $T_j$



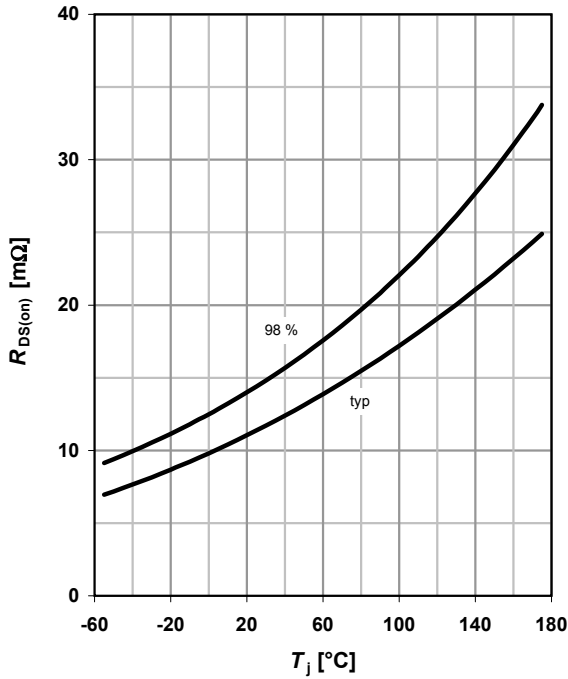
**8 Typ. forward transconductance**

$g_{fs} = f(I_D); T_j = 25\text{ }^\circ\text{C}$



**9 Drain-source on-state resistance**

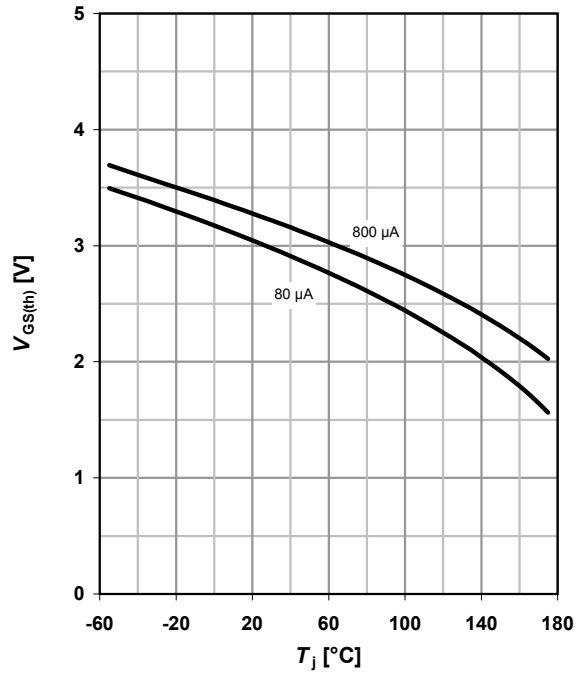
$R_{DS(on)} = f(T_j); I_D = 50 \text{ A}; V_{GS} = 10 \text{ V}$



**10 Typ. gate threshold voltage**

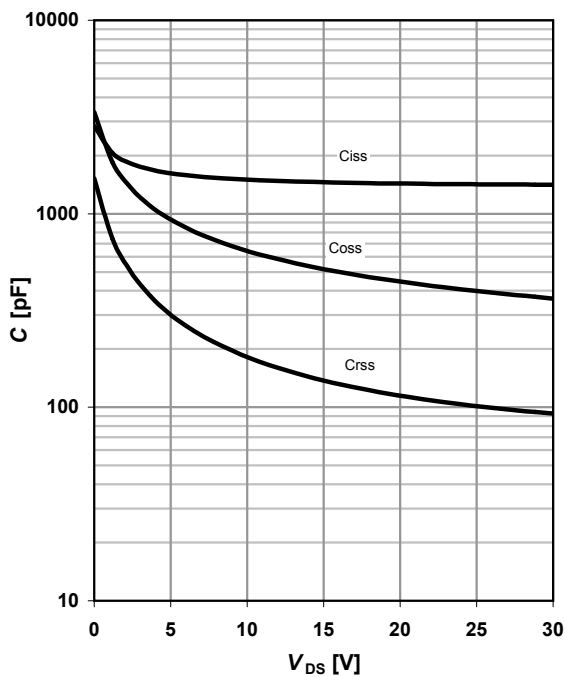
$V_{GS(th)} = f(T_j); V_{GS} = V_{DS}$

parameter:  $I_D$



**11 Typ. capacitances**

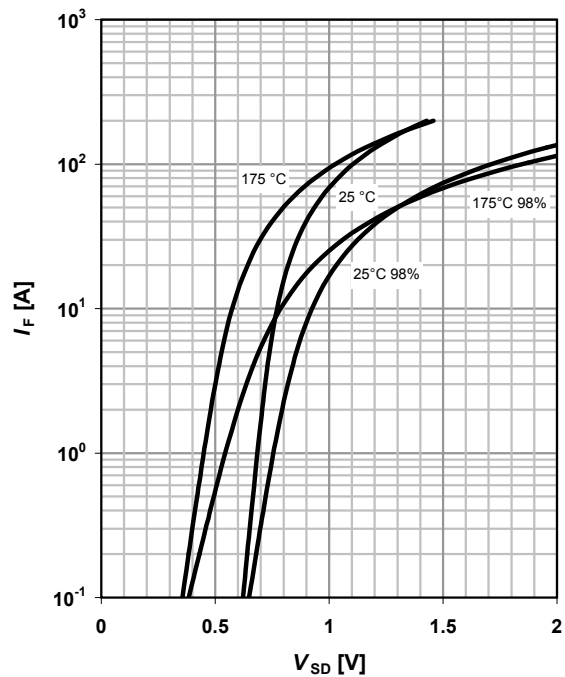
$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$



**12 Forward characteristics of reverse diode**

$I_F = f(V_{SD})$

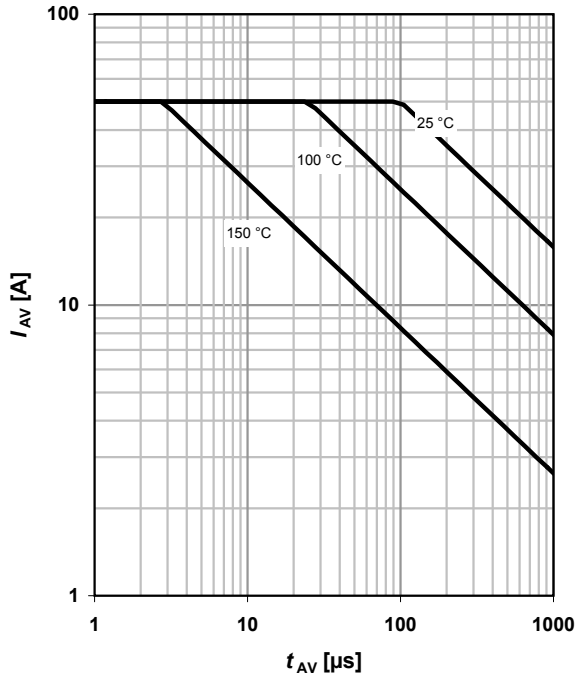
parameter:  $T_j$



**13 Avalanche characteristics**

$I_{AS}=f(t_{AV}); R_{GS}=25 \Omega$

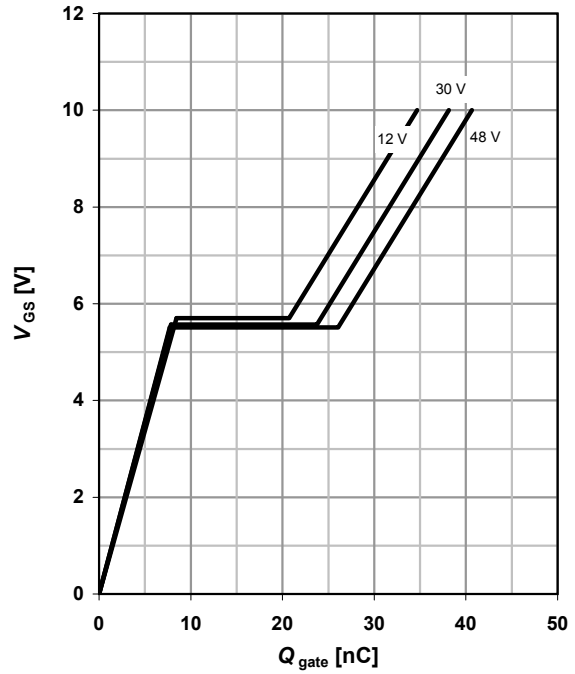
parameter:  $T_{j(start)}$



**14 Typ. gate charge**

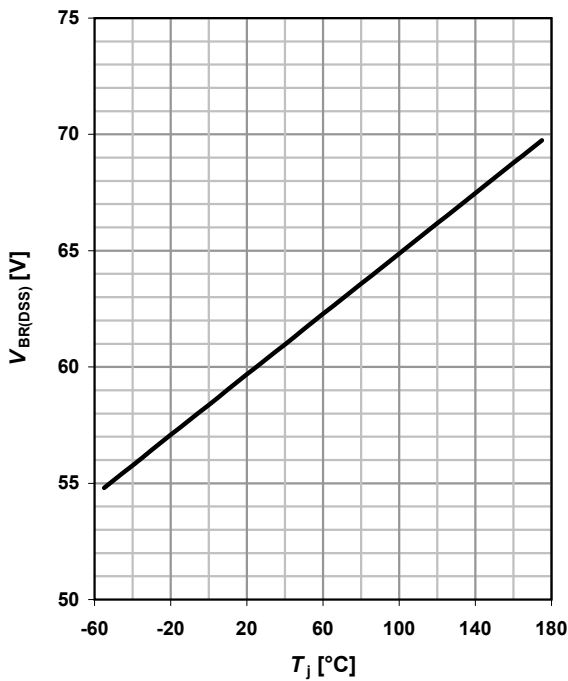
$V_{GS}=f(Q_{gate}); I_D=50 \text{ A pulsed}$

parameter:  $V_{DD}$

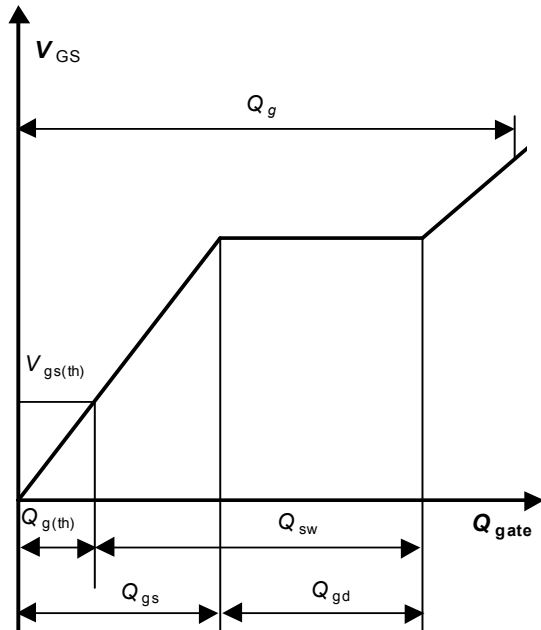


**15 Drain-source breakdown voltage**

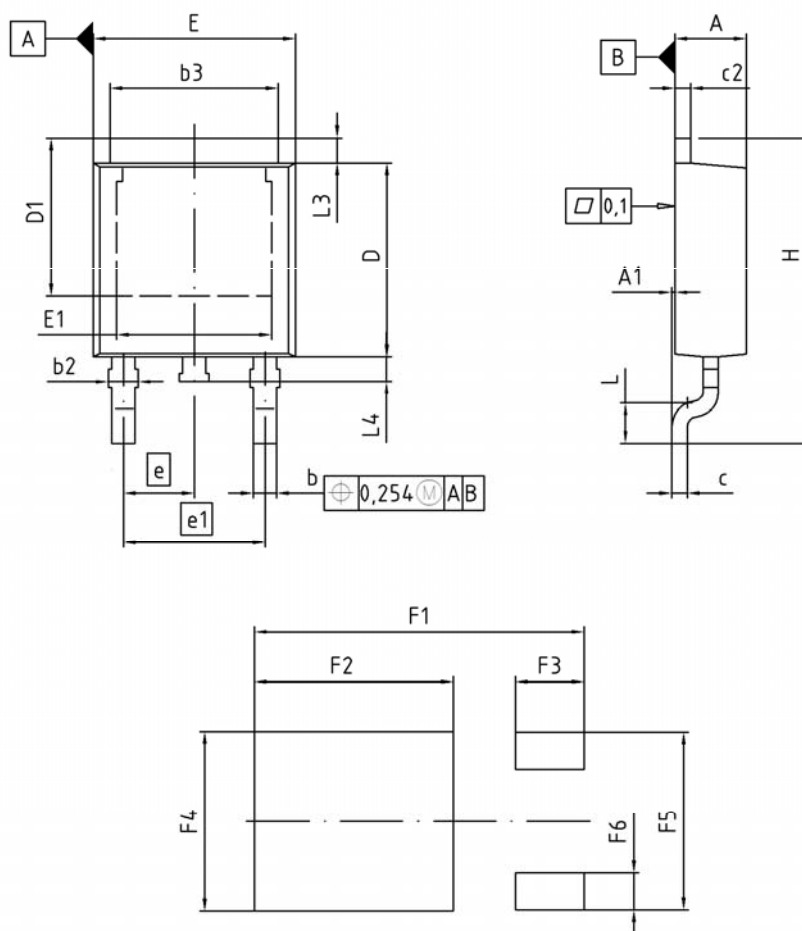
$V_{BR(DSS)}=f(T_j); I_D=1 \text{ mA}$



**16 Gate charge waveforms**



PG-TO252-3: Outline



| DIM | MILLIMETERS |       | INCHES |       |
|-----|-------------|-------|--------|-------|
|     | MIN         | MAX   | MIN    | MAX   |
| A   | 2.16        | 2.41  | 0.085  | 0.095 |
| A1  | 0.00        | 0.15  | 0.000  | 0.006 |
| b   | 0.64        | 0.89  | 0.025  | 0.035 |
| b2  | 0.65        | 1.15  | 0.026  | 0.045 |
| b3  | 5.00        | 5.50  | 0.197  | 0.217 |
| c   | 0.46        | 0.60  | 0.018  | 0.024 |
| c2  | 0.46        | 0.98  | 0.018  | 0.039 |
| D   | 5.97        | 6.22  | 0.235  | 0.245 |
| D1  | 5.02        | 5.84  | 0.198  | 0.230 |
| E   | 6.40        | 6.73  | 0.252  | 0.265 |
| E1  | 4.70        | 5.21  | 0.185  | 0.205 |
| e   | 2.29        |       | 0.090  |       |
| e1  | 4.57        |       | 0.180  |       |
| N   | 3           |       | 3      |       |
| H   | 9.40        | 10.48 | 0.370  | 0.413 |
| L   | 1.18        | 1.70  | 0.046  | 0.067 |
| L3  | 0.90        | 1.25  | 0.035  | 0.049 |
| L4  | 0.51        | 1.00  | 0.020  | 0.039 |
| F1  | 10.50       | 10.70 | 0.413  | 0.421 |
| F2  | 6.30        | 6.50  | 0.248  | 0.256 |
| F3  | 2.10        | 2.30  | 0.083  | 0.091 |
| F4  | 5.70        | 5.90  | 0.224  | 0.232 |
| F5  | 5.66        | 5.86  | 0.223  | 0.231 |
| F6  | 1.10        | 1.30  | 0.043  | 0.051 |

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